

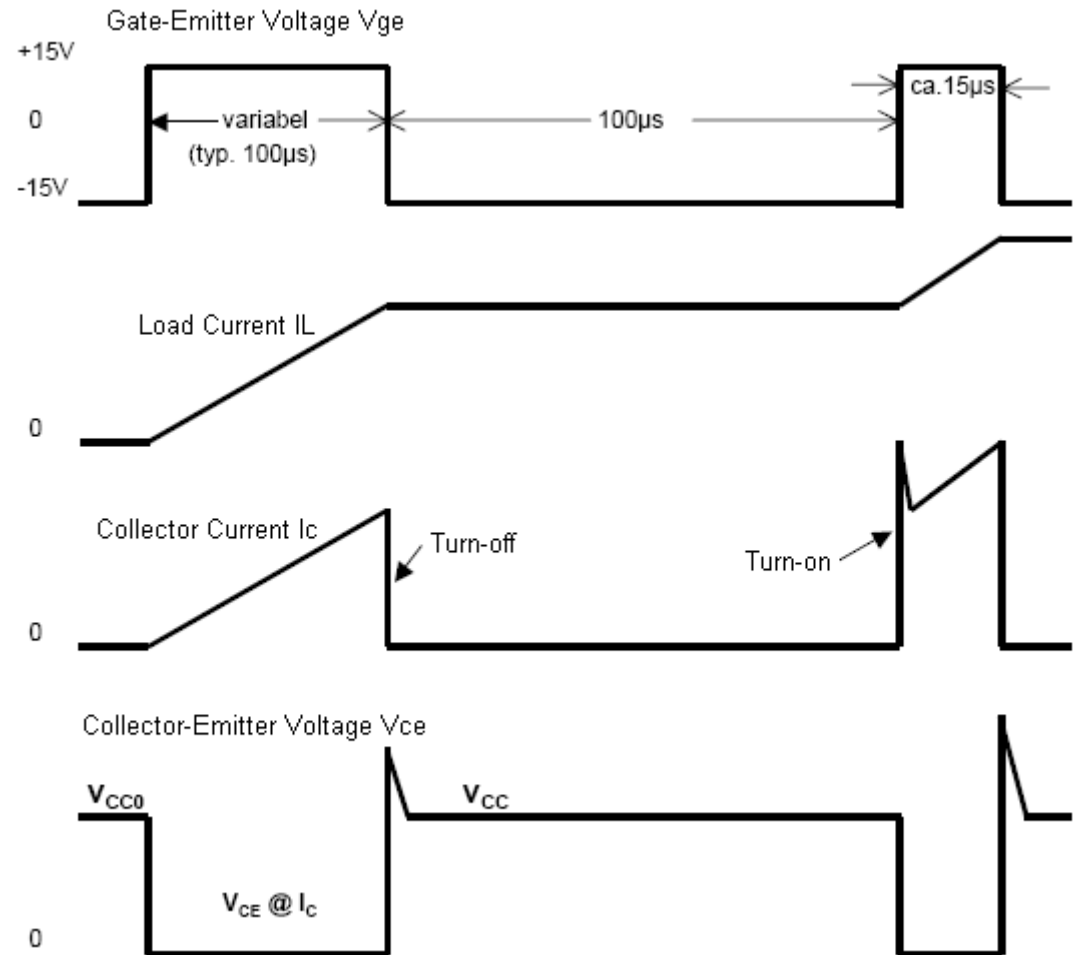
Double Pulse Test for IGBT & FWD

– Principle

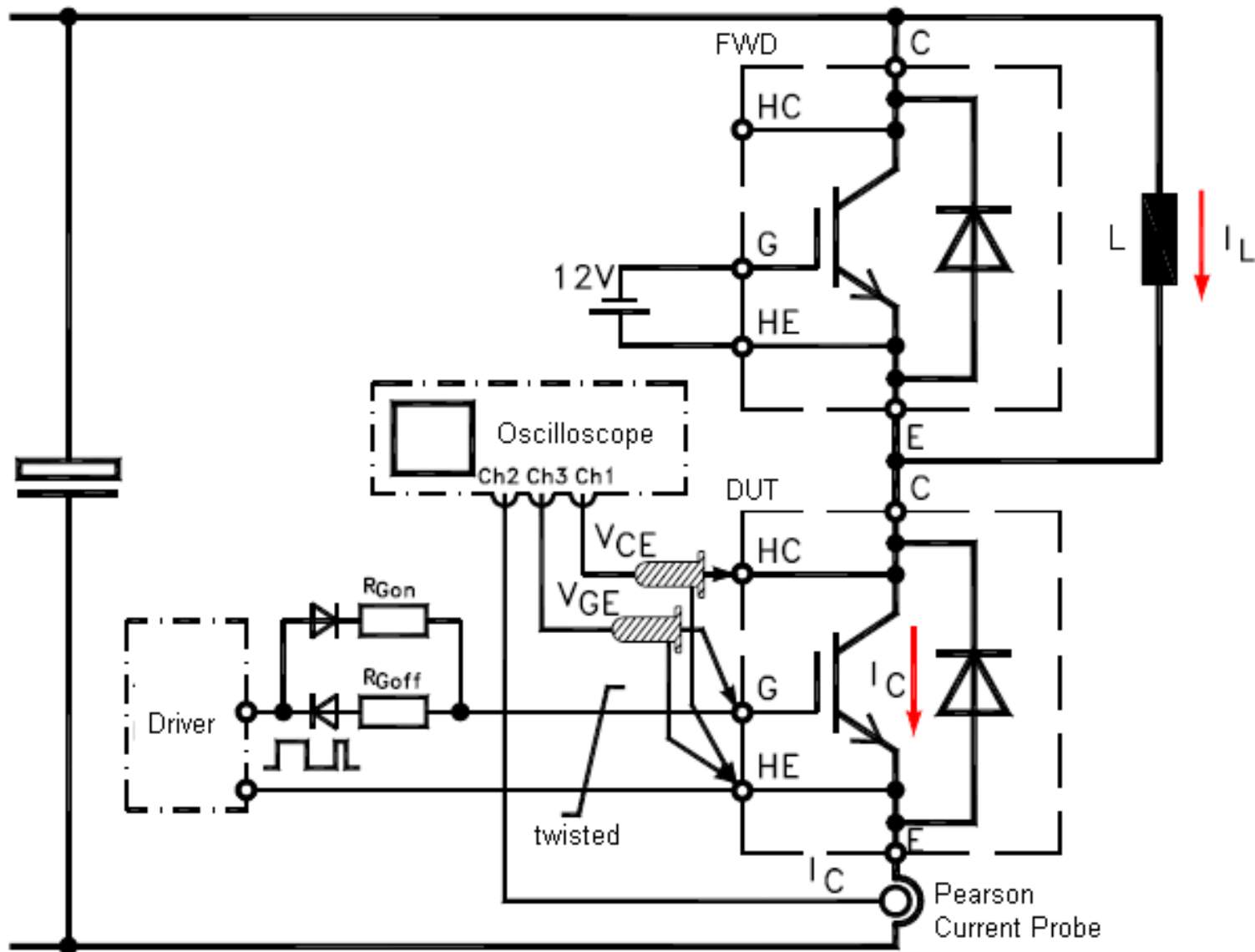


Double pulse test for IGBT/FWD

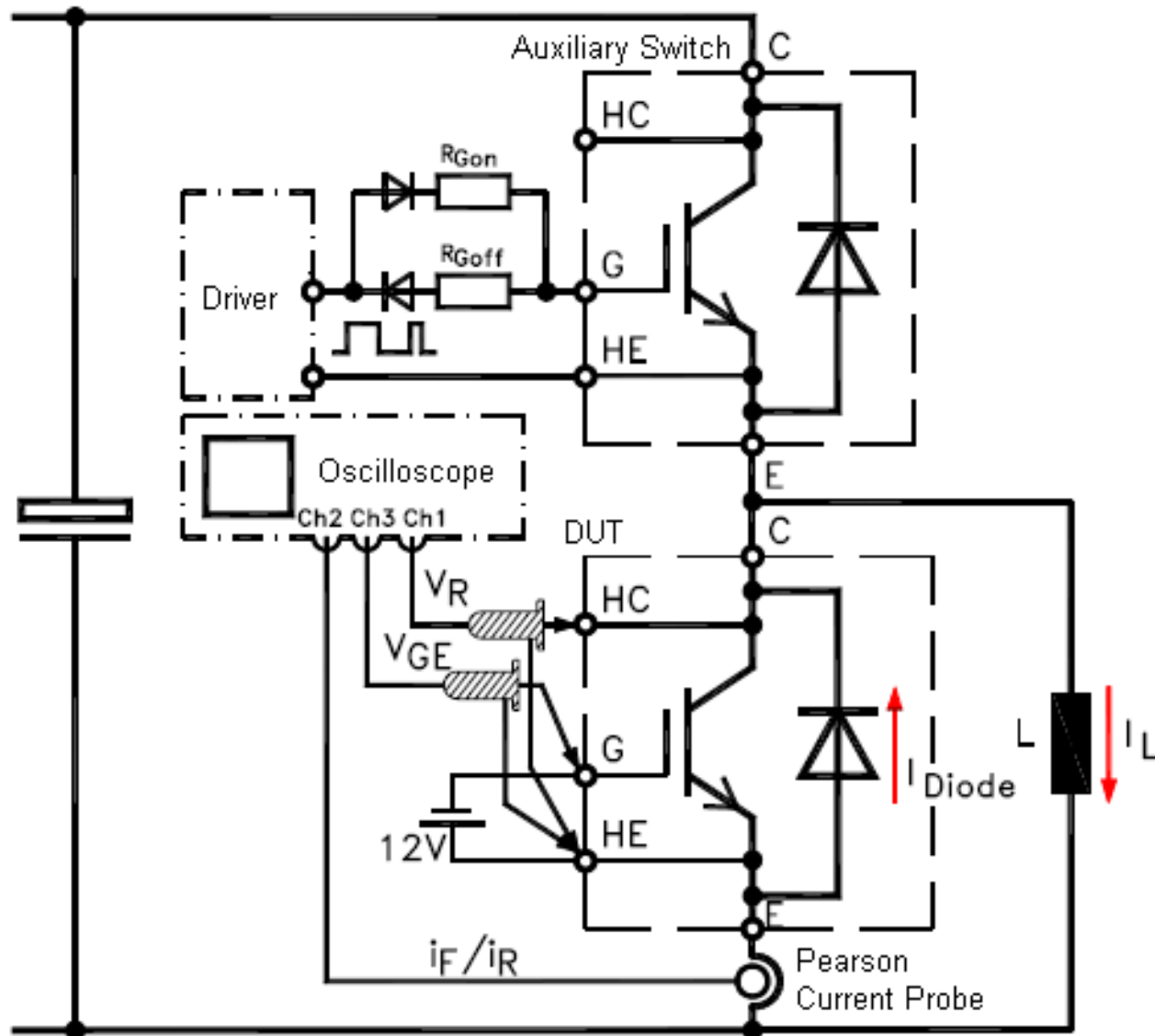
- The 1st turn-on pulse establishes desired current value (e.g. I_{cnom} for IGBT characterization or $2 \times I_{cnom}$ for RBSOA test) in the inductive load (inductor in the test).
- Turn-off of the 1st pulse creates current in free-wheeling diode (FWD). Due to the high load inductance and short turn-off period, the load current is almost constant in this interval.
- The 2nd turn-on pulse results in reverse recovery of the FWD hence the current overshoot in the test IGBT (like that in real applications).
- V_{ce} overshoot at turn-off of the 2nd pulse should be kept below IGBT blocking voltage (V_{ces}).



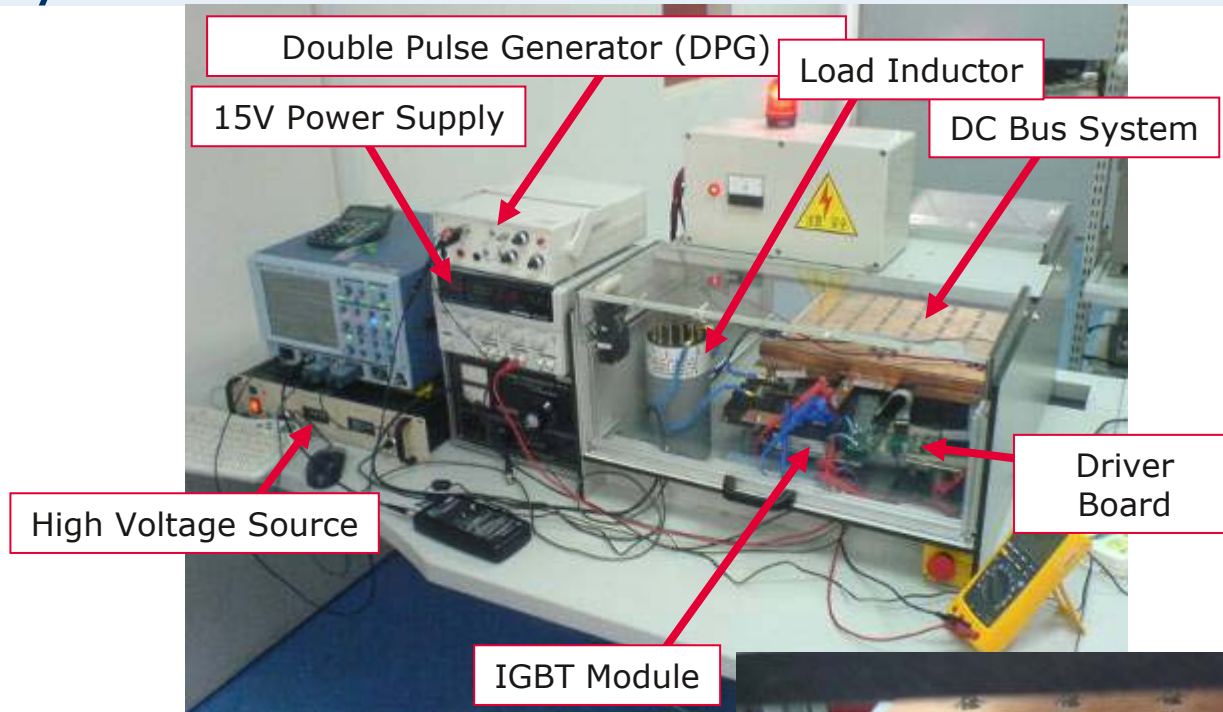
IGBT test schematic principle



FWD test principle



Dynamic Characteristics Test





We commit.
We innovate.
We partner.
We create value.



Never stop thinking